



FDMS8020

N-Channel PowerTrench[®] MOSFET 30 V, 131 A, 2.5 mΩ

Features

- Max $r_{DS(on)}$ = 2.5 mΩ at $V_{GS} = 10\text{ V}$, $I_D = 26\text{ A}$
- Max $r_{DS(on)}$ = 3.6 mΩ at $V_{GS} = 4.5\text{ V}$, $I_D = 21.5\text{ A}$
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- Next generation enhanced body diode technology, engineered for soft recovery
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

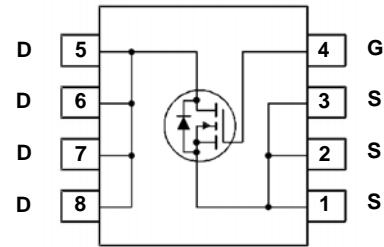
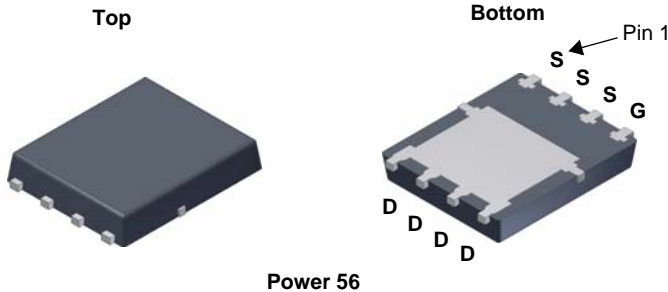


General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(on)}$, fast switching speed and body diode reverse recovery performance.

Applications

- VRM Vcore Switching For Desktop And Server
- OringFET / Load Switching
- DC-DC Conversion
- Motor Bridge Switch



MOSFET Maximum Ratings $T_A = 25\text{ °C}$ unless otherwise noted.

| Symbol | Parameter | Ratings | Units |
|----------------|---|-------------|--------------------|
| V_{DS} | Drain to Source Voltage | 30 | V |
| V_{GS} | Gate to Source Voltage (Note 4) | ± 20 | V |
| I_D | Drain Current -Continuous $T_C = 25\text{ °C}$ (Note 6) | 131 | A |
| | -Continuous $T_C = 100\text{ °C}$ (Note 6) | 83 | |
| | -Continuous $T_A = 25\text{ °C}$ (Note 1a) | 26 | |
| | -Pulsed (Note 5) | 507 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 3) | 93 | mJ |
| P_D | Power Dissipation $T_C = 25\text{ °C}$ | 65 | W |
| | Power Dissipation $T_A = 25\text{ °C}$ (Note 1a) | 2.5 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | $^{\circ}\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|-----|-----------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | 1.9 | $^{\circ}\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient (Note 1a) | 50 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|----------|----------|-----------|------------|------------|
| FDMS8020 | FDMS8020 | Power 56 | 13 " | 12 mm | 3000 units |

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|----|----|-----|----------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$ | 30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ | | 14 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$ | | | 1 | μA |
| I_{GSS} | Gate to Source Leakage Current, Forward | $V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$ | | | 100 | nA |

On Characteristics

| | | | | | | |
|--|--|--|-----|-----|-----|----------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$ | 1.0 | 1.5 | 3.0 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ | | -6 | | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{ V}$, $I_D = 26\text{ A}$ | | 2.0 | 2.5 | m Ω |
| | | $V_{GS} = 4.5\text{ V}$, $I_D = 21.5\text{ A}$ | | 2.6 | 3.6 | |
| | | $V_{GS} = 10\text{ V}$, $I_D = 26\text{ A}$, $T_J = 125\text{ }^\circ\text{C}$ | | 2.9 | 3.7 | |
| g_{FS} | Forward Transconductance | $V_{DS} = 5\text{ V}$, $I_D = 26\text{ A}$ | | 154 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|--|------|------|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$ | | 2855 | 3800 | pF |
| C_{oss} | Output Capacitance | | | 1050 | 1400 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 115 | 175 | pF |
| R_g | Gate Resistance | | | 0.9 | | Ω |

Switching Characteristics

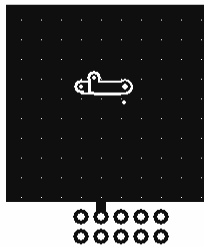
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|--------------|-------------------------------|--|---|-----|-----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 15\text{ V}$, $I_D = 26\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$ | | 12 | 22 | ns | |
| t_r | Rise Time | | | 5.7 | 12 | ns | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 32 | 52 | ns | |
| t_f | Fall Time | | | 4 | 10 | ns | |
| Q_g | Total Gate Charge | | $V_{GS} = 0\text{ V to }10\text{ V}$ | | 43 | 61 | nC |
| Q_g | Total Gate Charge | $V_{GS} = 0\text{ V to }4.5\text{ V}$ | $V_{DD} = 15\text{ V}$, $I_D = 26\text{ A}$ | | 21 | 29 | nC |
| Q_{gs} | Gate to Source Charge | | | | 7.3 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | | 6.0 | | nC |

Drain-Source Diode Characteristics

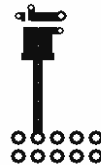
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|----------|---------------------------------------|--|--|------|-----|----|
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{ V}$, $I_S = 2.1\text{ A}$ (Note 2) | | 0.68 | 1.1 | V |
| | | $V_{GS} = 0\text{ V}$, $I_S = 26\text{ A}$ (Note 2) | | 0.78 | 1.2 | |
| t_{rr} | Reverse Recovery Time | $I_F = 26\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ | | 37 | 58 | ns |
| Q_{rr} | Reverse Recovery Charge | | | 18 | 33 | nC |
| t_{rr} | Reverse Recovery Time | $I_F = 26\text{ A}$, $di/dt = 300\text{ A}/\mu\text{s}$ | | 30 | 48 | ns |
| Q_{rr} | Reverse Recovery Charge | | | 36 | 57 | nC |

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta CA}$ is determined by the user's board design.



a) 50 $^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b) 125 $^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

3. Starting $T_J = 25\text{ }^\circ\text{C}$; N-ch: $L = 0.3\text{ mH}$, $I_{AS} = 25\text{ A}$, $V_{DD} = 27\text{ V}$, $V_{GS} = 10\text{ V}$.

4. As an N-ch device, the negative V_{GS} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

5. Pulsed I_D please refer to SOA curve for more details.

6. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

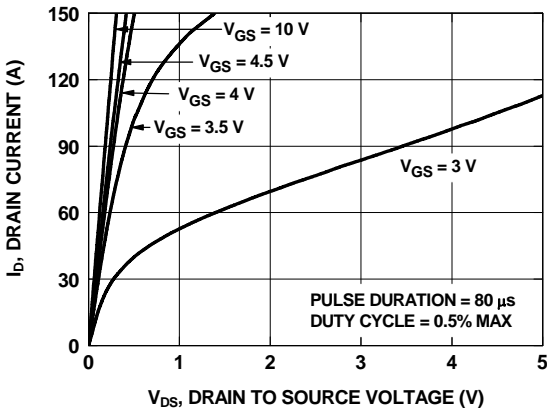


Figure 1. On-Region Characteristics

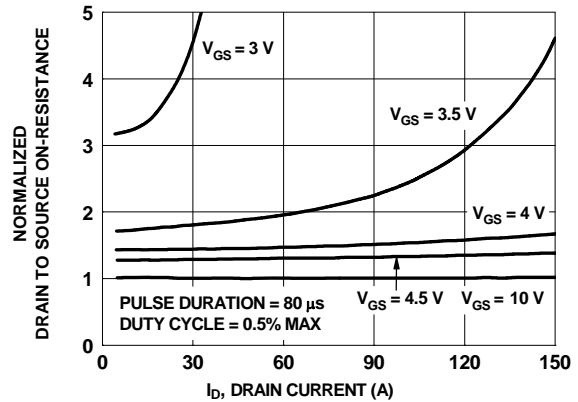


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

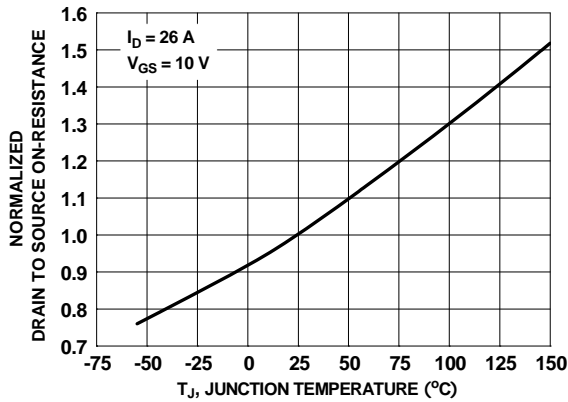


Figure 3. Normalized On-Resistance vs. Junction Temperature

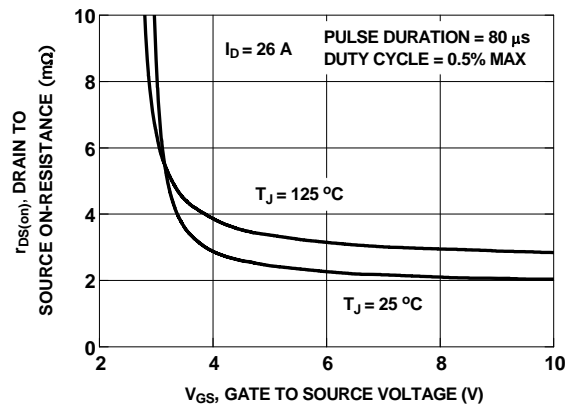


Figure 4. On-Resistance vs. Gate to Source Voltage

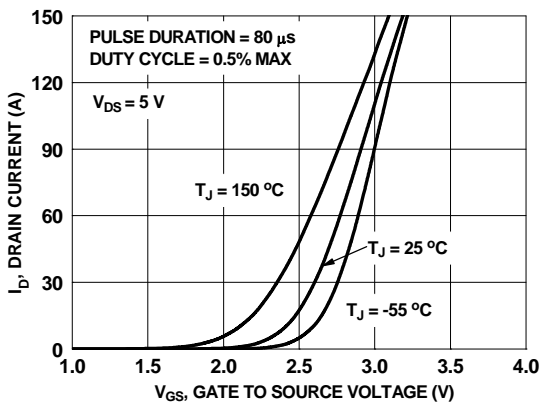


Figure 5. Transfer Characteristics

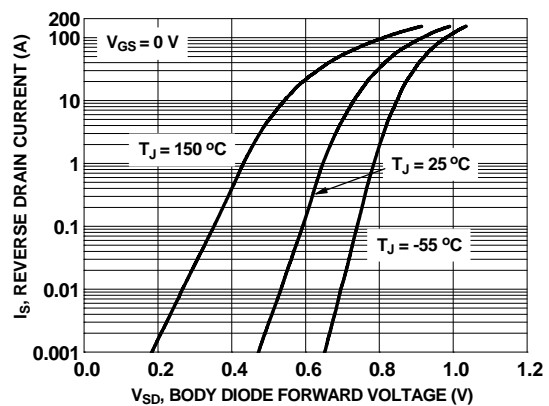


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

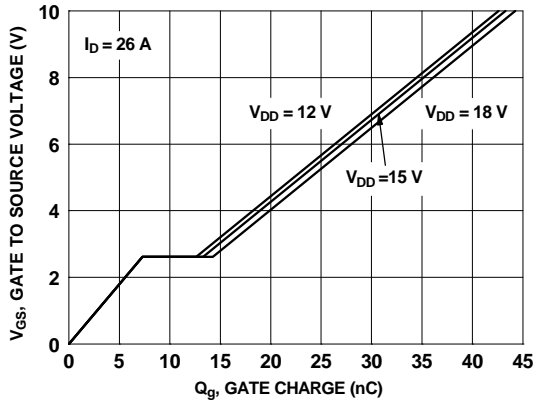


Figure 7. Gate Charge Characteristics

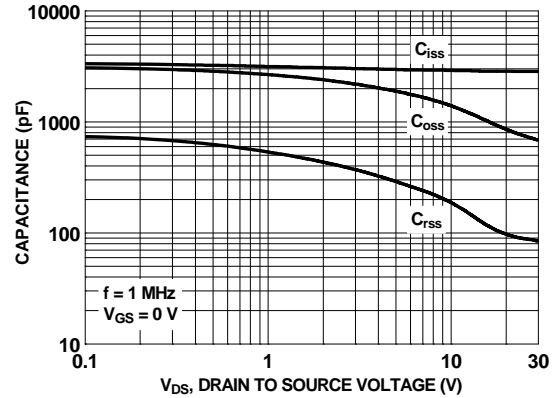


Figure 8. Capacitance vs. Drain to Source Voltage

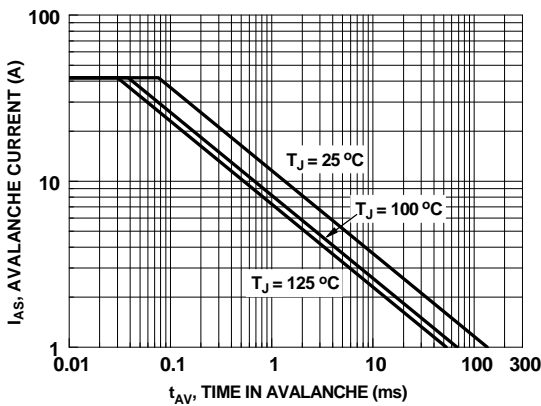


Figure 9. Unclamped Inductive Switching Capability

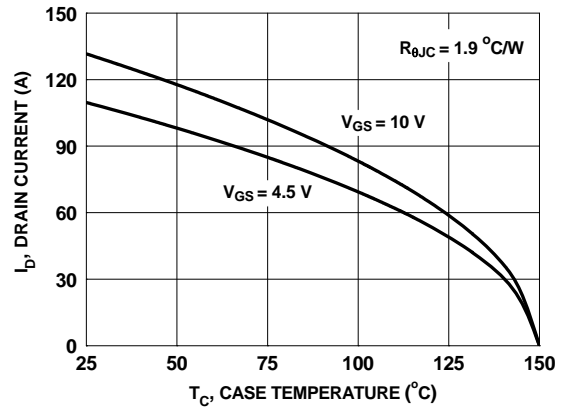


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

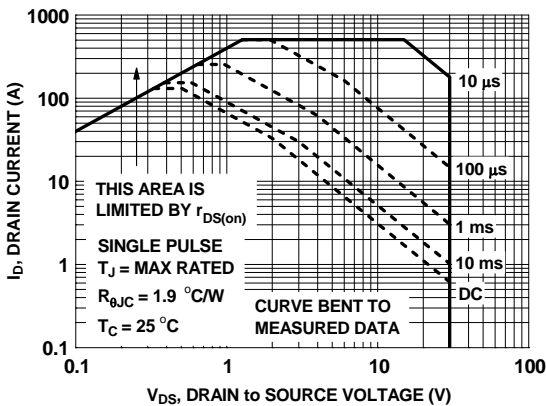


Figure 11. Forward Bias Safe Operating Area

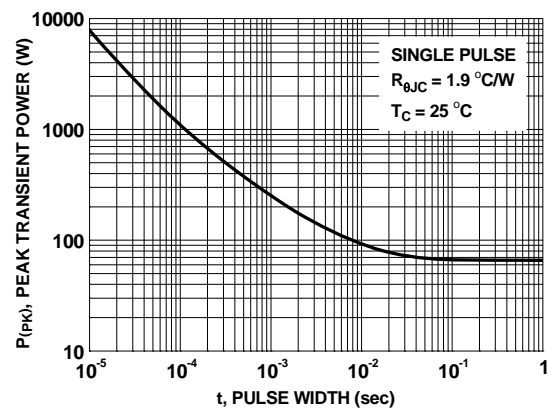


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted.

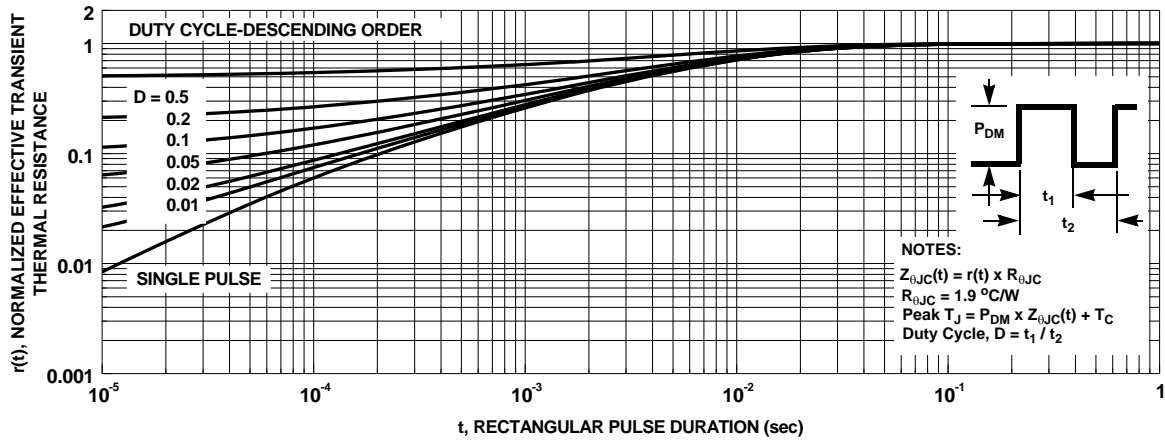
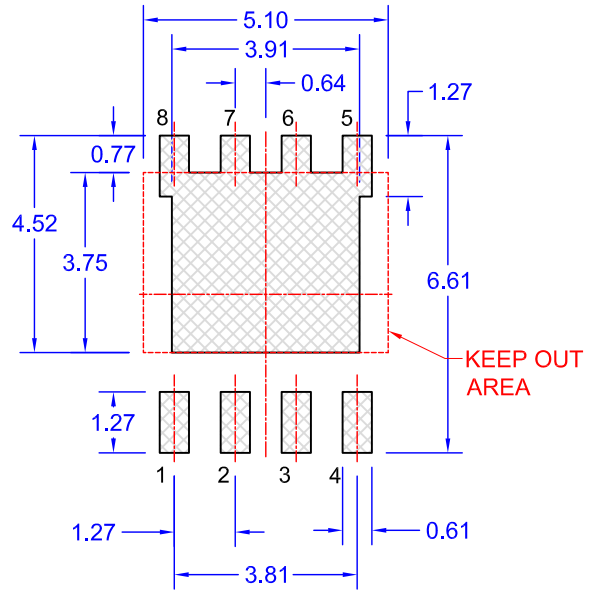


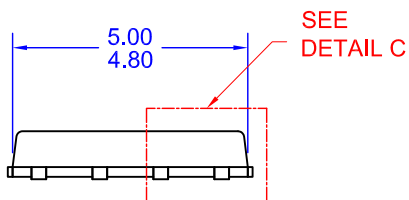
Figure 13. Junction-to-Case Transient Thermal Response Curve



TOP VIEW

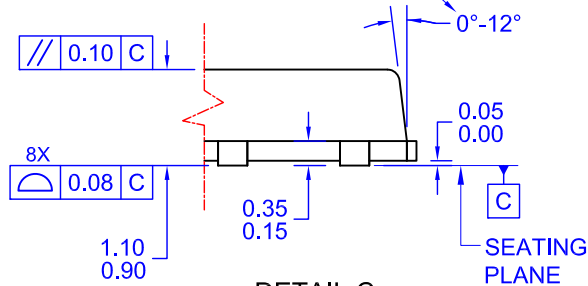


LAND PATTERN RECOMMENDATION

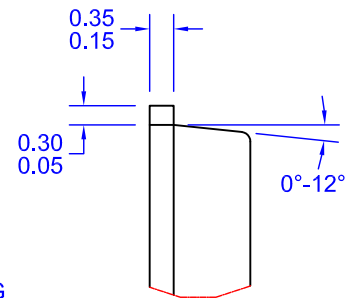


SIDE VIEW

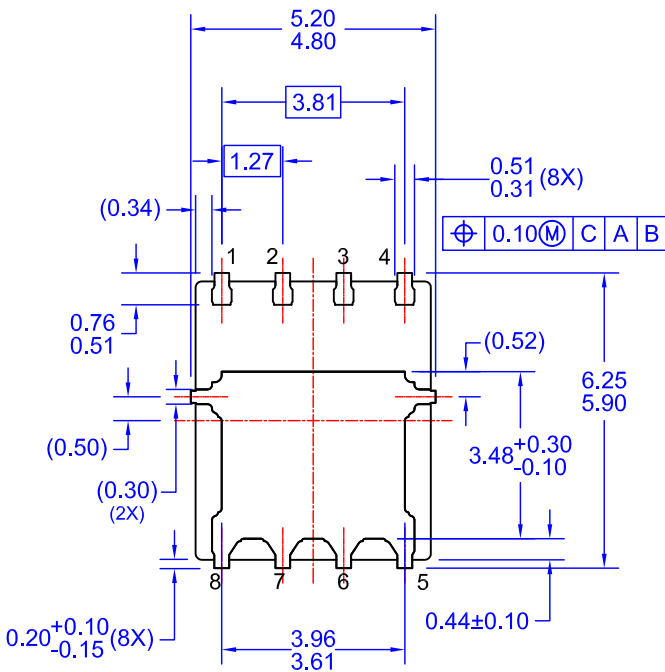
OPTIONAL DRAFT ANGLE MAY APPEAR ON FOUR SIDES OF THE PACKAGE



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- A. PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA, DATED OCTOBER 2002.
- B. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E. IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.
- F. DRAWING FILE NAME: PQFN08AREV10



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